Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Vishay/Siliconix SI4920DY-T1-E3

For any questions, you can email us directly: sales@integrated-circuit.com





Si4920DY

Vishay Siliconix

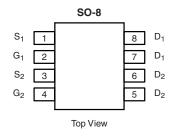
Dual N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	
30	0.025 at V _{GS} = 10 V	± 6.9	
	0.035 at V _{GS} = 4.5 V	± 5.8	

FEATURES

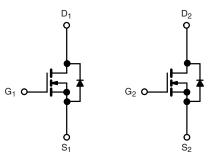
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4920DY-T1-E3 (Lead (Pb)-free)

Si4920DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	30	V		
Gate-Source Voltage		V _{GS} ± 20		\neg		
Continuous Drain Current /T 150 °C\8	T _A = 25 °C	I-	± 6.9			
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	- I _D	± 5.5	Α		
Pulsed Drain Current (10 µs Pulse Width)		I _{DM} ± 40		A		
Continuous Source Current (Diode Conduction) ^a		I _S 1.7]		
Marrian David District	T _A = 25 °C	P _D	2	w		
Maximum Power Dissipation ^a	T _A = 70 °C	טי	1.3			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	62.5	°C/W	

Notes:

a. Surface Mounted on FR4 board, $t \le 10$ s.

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Datasheet of SI4920DY-T1-E3 - MOSFET 2N-CH 30V 8-SOIC

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SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$			± 100	nA	
Zoro Coto Voltogo Droin Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			1	μΑ	
Zero Gate Voltage Drain Current					25		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
	B .	$V_{GS} = 10 \text{ V}, I_D = 6.9 \text{ A}$		0.020	0.025		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 5.8 \text{ A}$		0.026	0.035	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 6.9 A		25		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 1.7 A, V _{GS} = 0 V			1.2	V	
Dynamic ^b							
Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 6.9 \text{ A}$		15	23	nC	
Total Gate Charge	Q _{gt}			30	50		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6.9 \text{ A}$		7.5			
Gate-Drain Charge	Q_{gd}			3.5			
Gate Resistance	R_g	f = 1 MHz		2	3	Ω	
Turn-On Delay Time	t _{d(on)}			12	20		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		10	20	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		60	90		
Fall Time	t _f			15	30		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, dI/dt = 100 A/μs		50	90		

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

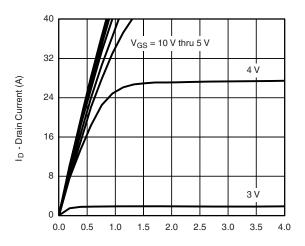




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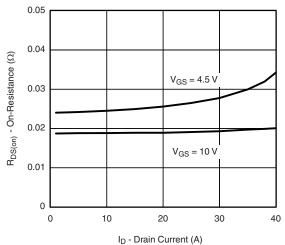
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

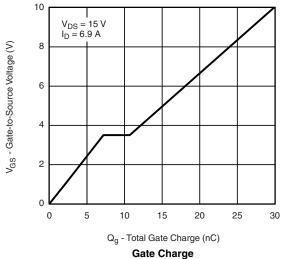


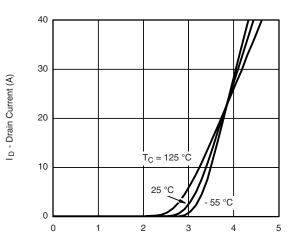
V_{DS} - Drain-to-Source Voltage (V)



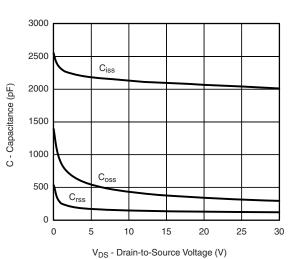


On-Resistance vs. Drain Current

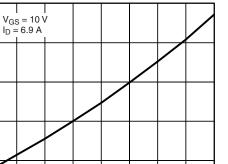




V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics**



Capacitance



100

125

150

T_J - Junction T emperature (°C)

Gate Charge On-Resistance vs. Junction Temperature

R_{DS(on)} - On-Resistance

(Normalized)

1.6

1.4

1.2

1.0

0.8

0.6

- 50 - 25

0

25

Document Number: 70667 www.vishay.com S09-0767-Rev. E, 04-May-09 3

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Datasheet of SI4920DY-T1-E3 - MOSFET 2N-CH 30V 8-SOIC

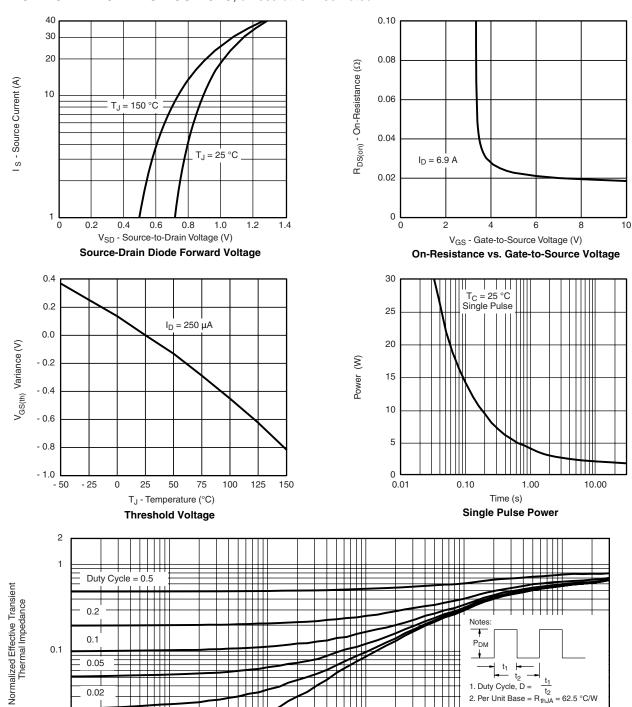
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Si4920DY

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Ambient

10⁻¹

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data see www.vishay.com/ppd?70667

10-2

Single Pulse

10-3

10

30

 $3.\,T_{JM}\cdot T_{A}=P_{DM}Z_{thJA}{}^{(t)}$

4. Surface Mounted

0.01

10-4



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Datasheet of SI4920DY-T1-E3 - MOSFET 2N-CH 30V 8-SOIC

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